Fernando Jose Sanchez

List of Publications by Year
in descending order

66 papers	2,929 citations	257450 24 h-index	168389 53 g-index
66 all docs	66 docs citations	66 times ranked	2304 citing authors

#	Article	IF	Citations
1	Dislocation Loop Generation Differences between Thin Films and Bulk in EFDA Pure Iron under Self-Ion Irradiation at 20 MeV. Metals, 2021, 11, 2000.	2.3	4
2	Ion Beam Experiments to Emulate Nuclear Fusion Environment on Structural Materials at CMAM. , 2020, , .		2
3	Study of damage in binary Fe85Cr15 alloys irradiated by ions and the effect of an external magnetic field during irradiation. Journal of Nuclear Materials, 2019, 517, 138-147.	2.7	11
4	Corrosion protective action of different coatings for the helium cooled pebble bed breeder concept. Journal of Nuclear Materials, 2019, 516, 160-168.	2.7	11
5	Nanoindentation and TEM to Study the Cavity Fate after Post-Irradiation Annealing of He Implanted EUROFER97 and EU-ODS EUROFER. Micromachines, 2018, 9, 633.	2.9	11
6	Radiation effects on deuterium permeation for PLD alumina coated Eurofer steel measured during 1.8â€¯MeV electron irradiation. Journal of Nuclear Materials, 2018, 512, 118-125.	2.7	21
7	Efficient hydrogen and deuterium permeation reduction in Al₂O₃ coatings with enhanced radiation tolerance and corrosion resistance. Nuclear Fusion, 2018, 58, 126007.	3.5	25
8	Ionizing radiation effects on the thermal stability of deuterium trapping in reaction bonded SiC. Journal of Nuclear Materials, 2018, 508, 219-225.	2.7	4
9	Corrosion mechanisms of Eurofer produced by lithium ceramics under fusion relevant conditions. Nuclear Materials and Energy, 2018, 15, 110-114.	1.3	16
10	Corrosion characteristics of reduced activation ferritic-martensitic steel EUROFER by Li2TiO3 with excess Li. Nuclear Materials and Energy, 2018, 15, 190-194.	1.3	15
11	Neutron shielding assessment for the Remote Handling Lower Port rack of ITER. Fusion Engineering and Design, 2018, 135, 50-58.	1.9	2
12	Displacement damage dose and implantation temperature effects on the trapping and release of deuterium implanted into SiC. Journal of Nuclear Materials, 2017, 493, 96-101.	2.7	6
13	Radiation induced deuterium absorption dependence on irradiation temperature, dose rate, and gas pressure for SiC. Fusion Engineering and Design, 2017, 124, 1127-1130.	1.9	1
14	Chemical compatibility study between ceramic breeder and EUROFER97 steel for HCPB-DEMO blanket. Journal of Nuclear Materials, 2017, 488, 196-203.	2.7	25
15	The effect of triple ion beam irradiation on cavity formation on pure EFDA iron. Journal of Nuclear Materials, 2016, 479, 100-111.	2.7	18
16	Trapping and thermal diffusion for energetic deuterium implanted into SiC. Nuclear Materials and Energy, 2016, 9, 383-387.	1.3	1
17	Influence of an external magnetic field on damage by self-ion irradiation in Fe 90 Cr 10 alloy. Nuclear Materials and Energy, 2016, 9, 476-479.	1.3	8
18	Optical absorption defects created in SiO2 by Si, O and He ion irradiation. Fusion Engineering and Design, 2014, 89, 1679-1683.	1.9	12

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19	Radiation induced deuterium absorption for RB-SiC, HP-SiC, silicon and graphite loaded during electron irradiation. Fusion Engineering and Design, 2014, 89, 2550-2553.	1.9	10
20	Optimization of surface morphology and electrical properties of Ti/Al/Tiâ€“W/Au ohmic contacts to n-GaN by two-step annealing method. Semiconductor Science and Technology, 2008, 23, 045021.	2.0	3
21	Monolithic uncooled IR detectors of polycrystalline PbSe: a real alternative. , 2007, 6542, 713.		16
22	Low resistance Tiâˆ•Alâˆ•Tiâ€“Wâˆ•Au Ohmic contact to n-GaN for high temperature applications. Applied Physics Letters, 2007, 90, 083504.	3.3	10
23	Performance enhancement of ohmic contact on n-GaN using Tiâ€“W as metal barrier. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2007, 143, 55-59.	3.5	3
24	Polycrystalline lead selenide: the resurgence of an old infrared detector. Opto-electronics Review, 2007, 15, .	2.4	32
25	A 32x32 array of polycrystalline PbSe opens up the market of very low cost MWIR sensitive photon detectors. , 2006, , .		8
26	Progress on monolithic integration of cheap IR FPAs of polycrystalline PbSe. , 2005, , .		8
27	Process technology to integrate polycrystalline uncooled PbSe infrared detectors on interference filters. , 2004, 5251, 97.		3
28	Progress on uncooled PbSe detectors for low-cost applications. , 2004, , .		8
29	Polycrystalline lead selenide xâ€“y addressed uncooled focal plane arrays. Infrared Physics and Technology, 2003, 44, 281-287.	2.9	22
30	Role of halogens in the mechanism of sensitization of uncooled PbSe infrared photodetectors. Journal of Applied Physics, 2003, 93, 1778-1784.	2.5	71
31	Monolithic integration of spectrally selective uncooled lead selenide detectors for low cost applications. Applied Physics Letters, 2003, 83, 2751-2753.	3.3	25
32	Polycrystalline PbSe x-y addressed uncooled FPAs. , 2003, , .		16
33	Thermal stability of Pt- and Ni-based Schottky contacts on GaN and Al0.31Ga0.69N. Semiconductor Science and Technology, 2002, 17, L47-L54.	2.0	40
34	Voltage-tunable two-colour quantum well infrared detector with Al-graded triangular confinement barriers. Semiconductor Science and Technology, 2001, 16, 285-288.	2.0	3
35	Reliability of Schottky Contacts on AlGaN. Physica Status Solidi A, 2001, 188, 367-370.	1.7	18
36	Effect of Dielectric Layers on the Performance of AlGaN-Based UV Schottky Photodiodes. Physica Status Solidi A, 2001, 188, 307-310.	1.7	0

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37	Analysis and modeling of AlxGa1â^'xN-based Schottky barrier photodiodes. Journal of Applied Physics, 2000, 88, 2081-2091.	2.5	97
38	Luminescence properties and defects in GaN nanocolumns grown by molecular beam epitaxy. Physical Review B, 2000, 62, 16826-16834.	3.2	345
39	Efecto del dopado con Si sobre la estructura de defectos en sistemas heteroepitaxiales GaN/AlN/Si(111). Boletin De La Sociedad Espanola De Ceramica Y Vidrio, 2000, 39, 468-471.	1.9	1
40	The effect of Si doping on the defect structure of GaN/AlN/Si(111). Applied Physics Letters, 1999, 74, 3362-3364.	3.3	55
41	High-speed, low-noise metalâ€“semiconductorâ€“metal ultraviolet photodetectors based on GaN. Applied Physics Letters, 1999, 74, 762-764.	3.3	175
42	High-quality visible-blind AlGaN p-i-n photodiodes. Applied Physics Letters, 1999, 74, 1171-1173.	3.3	145
43	Growth of III-nitrides on Si(111) by molecular beam epitaxy Doping, optical, and electrical properties. Journal of Crystal Growth, 1999, 201-202, 296-317.	1.5	189
44	MBE growth of GaN and AlGaN layers on Si(111) substrates: doping effects. Journal of Crystal Growth, 1999, 201-202, 415-418.	1.5	20
45	Band-gap narrowing and potential fluctuation in Si-doped GaN. Applied Physics Letters, 1999, 74, 102-104.	3.3	88
46	The effect of the III/V ratio and substrate temperature on the morphology and properties of GaN- and AlN-layers grown by molecular beam epitaxy on Si(1 1 1). Journal of Crystal Growth, 1998, 183, 23-30.	1.5	303
47	Growth optimization and doping with Si and Be of high quality GaN on Si(111) by molecular beam epitaxy. Journal of Electronic Materials, 1998, 27, 276-281.	2.2	37
48	High-performance GaN p-n junction photodetectors for solar ultraviolet applications. Semiconductor Science and Technology, 1998, 13, 1042-1046.	2.0	205
49	Experimental evidence for a Be shallow acceptor in GaN grown on Si(111) by molecular beam epitaxy. Semiconductor Science and Technology, 1998, 13, 1130-1133.	2.0	43
50	Effect of Ga/Si interdiffusion on optical and transport properties of GaN layers grown on Si(111) by molecular-beam epitaxy. Physical Review B, 1998, 58, 1550-1559.	3.2	92
51	Analysis of the Visible and UV Electroluminescence in Homojunction GaN LED's. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	30
52	Crystal Morphology and Optical Emissions of GaN layers grown on Si(111) substrates by Molecular Beam Epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	5
53	Reactive ion etching of GaN layers using. Semiconductor Science and Technology, 1997, 12, 1654-1657.	2.0	37
54	Photoconductor gain mechanisms in GaN ultraviolet detectors. Applied Physics Letters, 1997, 71, 870-872.	3.3	163

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55	Growth kinetics and morphology of high quality AlN grown on Si(111) by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 1997, 82, 4681-4683.	2.5	62
56	Study of high quality AlN layers grown on Si(111) substrates by plasma-assisted molecular beam epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1.	1.0	14
57	Characterization and Modeling of Photoconductive GaN Ultraviolet Detectors. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1.	1.0	13
58	XPS study of Au/GaN and Pt/GaN contacts. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1.	1.0	23
59	Yellow luminescence and related deep states in undoped GaN. Physical Review B, 1997, 55, 4689-4694.	3.2	203
60	Exciton and donor - acceptor recombination in undoped GaN on Si(111). Semiconductor Science and Technology, 1997, 12, 1396-1403.	2.0	53
61	Yellow luminescence in Mg-doped GaN. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1.	1.0	9
62	Yellow Band and Deep levels in Undoped MOVPE GaN.. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1.	1.0	18
63	Optical and electrical characterization of GaN layers grown on silicon and sapphire substrates. Solid-State Electronics, 1996, 40, 81-84.	1.4	2
64	Behavior of silicon-, sulfur-, and tellurium-relatedDXcenters in liquid-phase-epitaxy and vapor-phase-epitaxyGaAs1âˆ’xPxalloys. Physical Review B, 1996, 53, 7736-7741.	3.2	6
65	Deep level transient spectroscopy assessment of silicon contamination in AlGaAs layers grown by metalorganic vapor phase epitaxy. Journal of Electronic Materials, 1995, 24, 1017-1022.	2.2	4
66	Fe⁺ Implantation Induced Damage in Oxide Dispersion Strengthened Steels Investigated by Doppler Broadening Spectroscopy. Defect and Diffusion Forum, 0, 373, 113-116.	0.4	3